

STR71xF

ARM7TDMI[™] 32-bit MCU with Flash, USB, CAN 5 timers, ADC, 10 communications interfaces

Features

Core

- ARM7TDMI 32-bit RISC CPU
- 59 MIPS @ 66 MHz from SRAM
- 45 MIPS @ 50 MHz from Flash

Memories

- Up to 256 Kbytes Flash program memory (10 kcycles endurance, 20 yrs retention @ 85° C)
- 16K bytes Flash data memory (100 kcycles endurance, 20 yrs retention@ 85° C)
- Up to 64 Kbytes RAM
- External Memory Interface (EMI) for up to 4 banks of SRAM, Flash, ROM
- Multi-boot capability

■ Clock, Reset and Supply Management

- 3.0 to 3.6V application supply and I/Os
- Internal 1.8V regulator for core supply
- Clock input from 0 to 16.5 MHz
- Embedded RTC osc. running from external 32 kHz crystal
- Embedded PLL for CPU clock
- Realtime Clock for clock-calendar function
- 5 power saving modes: SLOW, WAIT, LPWAIT, STOP and STANDBY modes

Nested interrupt controller

- Fast interrupt handling with multiple vectors
- 32 vectors with 16 IRQ priority levels
- 2 maskable FIQ sources



Up to 48 I/O ports

 - 30/32/48 multifunctional bidirectional I/Os Up to 14 ports with interrupt capability

5 Timers

- 16-bit watchdog timer
- 3 16-bit timers with 2 input captures, 2 output compares, PWM and pulse counter
- 16-bit timer for timebase functions

10 Communications Interfaces

- 2 I²C interfaces (1 multiplexed with SPI)
- 4 UART asynchronous serial interfaces
- Smart Card ISO7816-3 interface on UART1
- 2 BSPI synchronous serial interfaces
- CAN interface (2.0B Active)
- USB Full Speed (12Mbit/s) Device Function with Suspend and Resume
- HDLC synchronous communications
- 4-channel 12-bit A/D Converter
 - Sampling frequency up to 1kHz
 - Conversion range: 0 to 2.5V
- Development tools support

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Note:	For detailed information on the STR710 Microcontroller memory, registers and peripherals, please refer to the STR710 Reference Manual.



1 Introduction

This datasheet provides the STR71x Ordering Information, Mechanical and Electrical Device Characteristics.

For complete information on the STR710 Microcontroller memory, registers and peripherals. please refer to the STR710 Reference Manual.

For information on programming, erasing and protection of the internal Flash memory please refer to the STR7 Flash Programming Reference Manual

For information on the ARM7TDMI core please refer to the ARM7TDMI Technical Reference Manual

2 Device summary

Features	STR710 FZ1	STR710 FZ2	STR710 RZ	STR711 FR0	STR711 FR1	STR711 FR2	STR712 FR0	STR712 FR1	STR712 FR2	STR715 FRx
Flash - Kbytes	128+16	256+16	0	64+16	128+16	256+16	64+16 128+16		256+16	64+16
RAM - Kbytes	32	64	64	16	32	64	16	32	64	16
Peripheral Functions	CAN, E	MI, USB,	48 I/Os	ι	JSB, 30 I/	Os	CAN, 32 I/Os 32 I/O			
Operating Voltage					3.0 t	o 3.6V				
Operating Temp.	-40 to +85°C or 0 to 70° C									
Packages	T=LQFP144 20 x 20 T=LQFP64 10 x10 / H=LFBGA64 8 x 8 x 1.7 H=LFBGA144 10 x10 T=LQFP64 10 x10 / H=LFBGA64 8 x 8 x 1.7									

Table 1. Device summary

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3 Description

ARM[®] core with embedded Flash & RAM

The STR710 series is a family of ARM-powered 32-bit Microcontrollers with embedded Flash and RAM. It combines the high performance ARM7TDMI CPU with an extensive range of peripheral functions and enhanced I/O capabilities. STR71xF devices have on-chip high-speed single voltage FLASH memory and high-speed RAM. STR710R devices have high-speed RAM but no internal Flash. The STR710 family has an embedded ARM core and is therefore compatible with all ARM tools and software.

Extensive tools support

STMicroelectronics' 32-bit, ARM core-based microcontrollers are supported by a complete range of high-end and low-cost development tools to meet the needs of application developers. This extensive line of hardware/software tools includes starter kits and complete development packages all tailored for ST's ARM core-based MCUs. The range of development packages includes third-party solutions that come complete with a graphical development environment and an in-circuit emulator/programmer featuring a JTAG application interface. These support a range of embedded operating systems (OS), while several royalty-free OSs are also available.

For more information, please refer to ST MCU site http://www.st.com/mcu



4 System architecture

Package Choice: Low Pin-Count 64-pin or Feature-Rich 144-pin LQFP or BGA

The STR710 family is available in 5 main versions.

The 144-pin versions have the full set of all features including CAN, USB and External Memory Interface (EMI).

- **STR710F:** 144-pin BGA or LQFP with CAN, USB and EMI
- STR710R: Flashless 144-pin BGA or LQFP with CAN, USB and EMI (no internal Flash memory)

The three 64-pin versions (BGA or LQFP) do not include External Memory Interface.

- **STR715F:** 64-pin BGA or LQFP without CAN or USB
- STR711F: 64-pin BGA or LQFP with USB
- STR712F: 64-pin BGA or LQFP with CAN

High Speed Flash Memory (STR71xF)

The Flash program memory is organized in two banks of 32-bit wide Burst Flash memories enabling true read-while-write (RWW) operation. Device Bank 0 is up to 256 Kbytes in size, typically for the application program code. Bank 1 is 16K bytes, typically used for storing data constants. Both banks are accessed by the CPU with zero wait states @ 33 MHz

Bank 0 memory endurance is 10K write/erase cycles and Bank 1 endurance is 100K write/erase cycles. Data retention is 20 years at 85°C on both banks. The two banks can be accessed independently in read or write. Flash memory can be accessed in two modes:

- Burst mode: 64-bit wide memory access at up to 50 MHz.
- Direct 32-bit wide memory access for deterministic operation at up to 33 MHz.

The STR7 embedded Flash memory can be programmed using In-Circuit Programming or In-Application programming.

IAP (In-Application Programming): The IAP is the ability to re-program the Flash memory of a microcontroller while the user program is running.

ICP (In-Circuit Programming): The ICP is the ability to program the Flash memory of a microcontroller using JTAG protocol while the device is mounted on the user application board.

The Flash memory can be protected against different types of unwanted access (read/write/erase). There are two types of protection:

- Sector Write Protection
- Flash Debug Protection (locks JTAG access)

Refer to the STR7 Flash Programming Reference manual for details.

Optional External Memory (STR710)

The non-multiplexed 16-bit data/24-bit address bus available on the STR710 (144-pin) supports four 16-Mbyte banks of external memory. Wait states are programmable individually for each bank allowing different memory types (Flash, EPROM, ROM, SRAM etc.) to be used to store programs or data.

Figure 1 shows the general block diagram of the device family.

Flexible Power Management

To minimize power consumption, you can program the STR710 to switch to SLOW, WAIT, LPWAIT (low power wait), STOP or STANDBY mode depending on the current system activity in the application.

Flexible Clock Control

Two external clock sources can be used, a main clock and a 32 kHz backup clock. The embedded PLL allows the internal system clock (up to 66 MHz) to be generated from a main clock frequency of 16 MHz or less. The PLL output frequency can be programmed using a wide selection of multipliers and dividers. The microcontroller core, APB1 and APB2 peripherals are in separate clock domains and can be programmed to run at different frequencies during application runtime. The clock to each peripheral is gated with an individual control bit to optimize power usage by turning off peripherals any time they are not required.

Voltage Regulators

The STR710 requires an external 3.0-3.6V power supply. There are two internal Voltage Regulators for generating the 1.8V power supply for the core and peripherals. The main VR is switched off during low power operation.

Low Voltage Detectors

Both the Main Voltage Regulator and the Low Power Voltage Regulator contain each a low voltage detection circuitry which keep the device under reset when the corresponding controlled voltage value (V_{18} or V_{18BKP}) falls below 1.35V (+/- 10%). This enhances the security of the system by preventing the MCU from going into an unpredictable state.

An external reset circuit must be used to provide the RESET at V_{33} power-up. It is not sufficient to rely on the RESET generated by the LVD in this case. This is because LVD operation is guaranteed only when V_{33} is within the specification.

4.1 On-chip peripherals

CAN Interface (STR710 and STR712)

The CAN module is compliant with the CAN specification V2.0 part B (active). The bit rate can be programmed up to 1 MBaud.

USB Interface (STR710 and STR711)

The full-speed USB interface is USB V2.0 compliant and provides up to 16 bidirectional/32 unidirectional endpoints, up to 12 Mb/s (full-speed), support for bulk transfer, isochronous transfers and USB Suspend/Resume functions.

Standard Timers

Each of the four timers have a 16-bit free-running counter with 7-bit prescaler

Three timers each provide up to two input capture/output compare functions, a pulse counter function, and a PWM channel with selectable frequency.

The fourth timer is not connected to the I/O ports. It can be used by the application software for general timing functions.



Realtime Clock (RTC)

The RTC provides a set of continuously running counters driven by the 32 kHz external crystal. The RTC can be used as a general timebase or clock/calendar/alarm function. When the STR710 is in Standby mode the RTC can be kept running, powered by the low power voltage regulator and driven by the 32 kHz external crystal.

UARTs

The 4 UARTs allow full duplex, asynchronous, communications with external devices with independently programmable TX and RX baud rates up to 1.25 Mb/s.

Smart Card Interface

UART1 is configurable to function either as a general purpose UART or as an asynchronous Smart Card interface as defined by ISO 7816-3. It includes Smart Card clock generation and provides support features for synchronous cards.

Buffered Serial Peripheral Interfaces (BSPI)

Each of the two SPIs allow full duplex, synchronous communications with external devices, master or slave communication at up to 5.5Mb/s in Master mode and 4 Mb/s in Slave mode.

I²C Interfaces

The two I^2C Interfaces provide multi-master and slave functions, support normal and fast I^2C mode (400 kHz) and 7 or 10-bit addressing modes.

One I²C Interface is multiplexed with one SPI, so either $2xSPI+1x I^2C$ or $1xSPI+2x I^2C$ may be used at a time.

HDLC interface

The High Level Data Link Controller (HDLC) unit supports full duplex operation and NRZ, NRZI, FM0 or MANCHESTER protocols. It has an internal 8-bit baud rate generator.

A/D Converter

The Analog to Digital Converter, converts in single channel or up to 4 channels in singleshot or round robin mode. Resolution is 12-bit with a sampling frequency of up to 1 kHz. The input voltage range is 0-2.5V.

Watchdog

The 16-bit Watchdog Timer protects the application against hardware or software failures and ensures recovery by generating a reset.

I/O Ports

The 48 I/O ports are programmable as Inputs or Outputs.

External Interrupts

Up to 14 external interrupts are available for application use or to wake-up the application from STOP mode.





Figure 1. STR710 block diagram



4.2 Related documentation

Available from www.arm.com:

ARM7TDMI Technical Reference Manual

Available from http://www.st.com:

STR71x Reference Manual

STR7 Flash Programming Reference Manual

AN1774 - STR710 Software development getting started

AN1775 - STR710 Hardware development getting started

AN1776 - STR710 Enhanced Interrupt Controller

AN1777 - STR710 Memory Mapping

AN1780 - Real Time Clock with STR710

AN1781 - Four 7 Segment Display Drive Using the STR710

The above is a selected list only, a full list STR71x application notes can be viewed at http://www.st.com.



4.3 Pin description for 144-pin packages





	Α	В	С	D	Е	F	G	Н	J	К	L	М		
1	P0.10	P2.0	P2.1	VSS	P2.2	P2.6	BOOT EN	P2.12	P2.13	P2.15	JTDI	N.C.		
2	VSS	RDn	P0.11	V33	P2.3	P2.8	P2.9	JTMS	JTRST n	TEST	TEST	N.C.		
3	V33	P0.9	P0.12	P0.13	P2.4	N.C.	P2.10	JTCK	NU	V33	N.C.	DBG RQS		
4	P0.6	P0.7	P0.8	P0.14	P2.5	N.C.	P2.11	JTDO	СК	СКОИТ	VSSIO- PLL	N.C.		
5	A.19	WEn.1	WEn.0	P0.5	P2.7	VSS	P2.14	N.C.	RTCX- TO	RTCXTI	N.C.	P0.15		
6	P0.3	A.15	A.16	A.17	A.18	V33	V18	N.C.	N.C.	V18BK P	VSS BKP	STDBY		
7	P0.2	P0.1	P0.4	VSS18	V18	A.14	D.12	D.1	D.0	nc	VSS18	RSTIN		
8	A.9	A.10	A.11	A.13	P0.0	A.0	D.11	P1.12/ CANTX	N.C.	AVSS	D.3	D.2		
9	VSS	V33	A.5	A.6	V33	D.15	D.10	P1.8	D.9	P1.0	N.C.	N.C.		
10	A.8	N.C.	P1.15	P1.13	VSS	D.14	USBDN	P1.7	D.8	P1.5	P1.1	D.4		
11	A.7	N.C.	P1.14	P1.10	A.2	D.13	USBDP	VSS	D.5	P1.4	P1.3	AVDD		
12	A.12	A.4	A.3	P1.9	A.1	P1.11/ CANRX	N.C.	V33IO- PLL	P1.6	D.7	D.6	P1.2		

Table 2. STR710 BGA ball connections

Legend / abbreviations for *Table 3*:

Type:

I = input, O = output, S = supply, HiZ= high impedance,

In/Output level: $C = CMOS \ 0.3V_{DD}/0.7V_{DD}$

 C_{T} = CMOS 0.3 V_{DD} /0.7 V_{DD} with input trigger T_T= TTL 0.8V/2V with input trigger

C/T = Programmable levels: CMOS 0.3V_{DD}/0.7V_{DD} or TTL 0.8V / 2V

Port and control configuration:

Input:	pu/pd= software enabled internal pull-up or pull down pu= in reset state, the internal 100k Ω weak pull-up is enabled. pd = in reset state, the internal 100k Ω weak pull-down is enabled.
Output:	OD = open drain (logic level) PP = push-pull T = true OD, (P-Buffer and protection diode to VDD not implemented), 5V tolerant.





Pir	n n°			•	Inp	ut	Οι	utpu	t	Stdby				
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	ΟD	ЬР	Active in Sto	Main function (after reset)	Altern	ate function	
												UART1: Receive Data input	UART1: Transmit data output.	
1	A1	P0.10/U1.RX/ U1.TX/ SC.DATA	I/O	pd	C _T	x	4mA	Т			Port 0.10	Note: This pin may be used for Smartcard DataIn/DataOut or single wire UART (half duplex) if programmed as Alternate Function Output. The pin will be tri-stated except when UART transmission is in progress		
2	B2	RD	0	5)					x		for externa		Active low read signal s to the OE_N input of	
3	C2	P0.11/BOOT.1 /U1.TX	I/O	pd	C _T		4mA	х	x		Port 0.11	Select Boot Configuration input UART1: Transmit data output.		
4	C3	P0.12/SC.CLK	I/O	pd	C _T		4mA	Х	Х		Port 0.12	Smartcard refer	rence clock output	
5	D1	V _{SS}	S								Ground vo	Itage for digital I/	Os ⁴⁾	
6	D2	V ₃₃	S								Supply vol	tage for digital I/0	Ds ⁴⁾	
7	B1	P2.0/CS.0	I/O	8)	CT		8mA	x	x		Port 2.0	Memory Bank (Note: This pin i	s forced to output le at reset to allow	
8	C1	P2.1/CS.1	I/O	pu 2)	C _T		8mA	х	х		Port 2.1	External Memo Memory Bank 1	ry Interface: Select output	
9	D3	P0.13/U2.RX/ T2.OCMPA	I/O	pu	CT	x	4mA	х	х		Port 0.13	UART2: Receive Data input	Timer2: Output Compare A output	
10	D4	P0.14/U2.TX/ T2.ICAPA	I/O	pu	С _Т		4mA	х	х		Port 0.14	UART2: Transmit data output	Timer2: Input Capture A input	
11	E1	P2.2/CS.2	I/O	pu 2)	CT		8mA	х	х		Port 2.2	External Memory Interface: Select Memory Bank 3 output		
12	E2	P2.3/CS.3	I/O	pu 2)	C _T		8mA	х	х		Port 2.3	External Memory Interface: Select Memory Bank 4 output		

 Table 3.
 STR710 pin description



Table 3. STR710 pin description

Pin	n°			1	Inp	ut	Οι	ıtpu	t	Stdby				
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	OD	ЬР	Active in Sto	Main function (after reset)	Alternate function		
13	E3	P2.4/A.20	I/O	pd 3)	CT		8mA	х	х		Port 2.4			
14	E4	P2.5/A.21	I/O	pd 3)	CT		8mA	х	х		Port 2.5	External Memory Interface: address bus		
15	F1	P2.6/A.22	I/O	pd 3)	CT		8mA	х	х		Port 2.6			
16	G1	BOOTEN	I		CT						Boot contro BOOT[1:0]	ol input. Enables sampling of pins		
17	E5	P2.7/A.23	I/O	pd 3)	CT		8mA	х	х		Port 2.7	External Memory Interface: address bus		
18	F2	P2.8	I/O	pu	C_{T}	Х	4mA	Х	Х		Port 2.8	External interrupt INT2		
19	F3	N.C.									Not conne	cted (not bonded)		
20	F4	N.C.									Not conne	cted (not bonded)		
21	F5	V _{SS}	S								Ground vo	Itage for digital I/Os ⁴⁾		
22	F6	V ₃₃	S								Supply vol	Supply voltage for digital I/Os ⁴⁾		
23	G2	P2.9	I/O	pu	C_T	Х	4mA	Х	Х		Port 2.9	External interrupt INT3		
24	G3	P2.10	I/O	pu	C_{T}	Х	4mA	Х	Х		Port 2.10	External interrupt INT4		
25	G4	P2.11	I/O	pu	CT	Х	4mA	Х	Х		Port 2.11	External interrupt INT5		
26	H1	P2.12	I/O	pu	C_{T}		4mA	Х	Х		Port 2.12			
27	J1	P2.13	I/O	pu	C_T		4mA	Х	Х		Port 2.13			
28	G5	P2.14	I/O	pu	C_{T}		4mA	Х	Х		Port 2.14			
29	K1	P2.15	I/O	pu	C_{T}		4mA	Х	Х		Port 2.15			
30	L1	JTDI	I		Τ _Τ						JTAG Data	input. External pull-up required.		
31	H2	JTMS	I		Τ _Τ						JTAG Mod required.	e Selection Input. External pull-up		
32	H3	JTCK	I		С						JTAG Cloc required.	k Input. External pull-up or pull-down		
33	H4	JTDO	0				8mA		Х		JTAG Data	a output. Note: Reset state = HiZ.		
34	J2	JTRST	I		Τ _Τ						JTAG Reset Input. External pull-up required.			
35	J3	NU									Reserved, must be forced to ground.			
36	K2	TEST									Reserved, must be forced to ground.			
37	M1	N.C.									Not connected (not bonded)			
38	L2	TEST									Reserved, must be forced to ground.			
39	L3	N.C.									Not connected (not bonded)			



Pir	n°			(le	Inp	ut	Οι	utpu	t	Stdby	Main			
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	OD	РР	Active in Ste	Main function (after reset)	Alternate function		
40	K3	V _{33IO-PLL}	S								Supply voltage for digital I/O circuitry and for PLL reference			
41	M4	N.C.									Not connec	cted (not bonded)		
42	L4	V _{SSIO-PLL}	S								Ground vol reference ⁴⁾	tage for digital I/O circuitry and for PLL		
43	M2	N.C.									Not connec	cted (not bonded)		
44	М3	DBGRQS	I		CT						Debug Mod	de request input (active high)		
45	K4	СКОИТ	0				8mA		х			ut (f _{PCLK2}) Note: Enabled by CKDIS APB Bridge 2		
46	J4	СК	Ι		С						Reference	clock input		
47	M5	P0.15/			Τ _T	x				х	Port 0.15	Wakeup from Standby mode input.		
77	WI5	WAKEUP			• 1	^				~	Note: This	port is input only.		
48	L5	N.C.									Not connected (not bonded)			
49	K5	RTCXTI									Realtime Clock input and input of 32 kHz oscillator amplifier circuit			
50	J5	RTCXTO									Output of 3	32 kHz oscillator amplifier circuit		
51	M6	STDBY	I/O		CT		4mA	x		х	low. Cautic select norm Output: Sta Software S Note : In St	tware Standby mode entry input active on: External pull-up to V_{33} required to nal mode. andby mode active low output following standby mode entry. tandby mode all pins are in high e except those marked Active in Stdby		
52	M7	RSTIN	1		Ст					Х	Reset inpu			
53	H5	N.C.			~ 1							cted (not bonded)		
54	L6	V _{SSBKP}			s					Х		n for low power voltage regulator.		
55	K6	V _{18BKP}			S					x	Stabilization for low power voltage regulator. Requires external capacitors of at least 1µF			
56	J6	N.C.									Not connected (not bonded)			
57	H6	N.C.									Not connected (not bonded)			
58	G6	V ₁₈	s								Stabilization for main voltage regulator. Requires external capacitors of at least 10μ F + 33nF between V ₁₈ and V _{SS18} . See <i>Figure 5</i> .			

Table 3.STR710 pin description



Table 3.	STR710 pin description
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Pir	ו n°	51 87 10 pm		-	Inp	ut	Οι	utpu	t	Stdby					
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	OD	РР	Active in Sto	Main function (after reset)	Alterr	nate function		
59	L7	V _{SS18}	S								Stabilizatio	on for main volta	ge regulator.		
60	K7	N.C.									Not connee	cted (not bonded	i)		
61	J7	D.0	I/O	6)			8mA								
62	H7	D.1	I/O	6)			8mA								
63	M8	D.2	I/O	6)			8mA				External M	lemory Interface	: data bus		
64	L8	D.3	I/O	6)			8mA								
65	M10	D.4	I/O	6)			8mA								
66	M11	V _{DDA}	S								Supply volt	tage for A/D Cor	iverter		
67	K8	V _{SSA}	S								Ground vo	Itage for A/D Co	nverter		
68	J8	N.C.									Not conne	cted (not bonded	1)		
69	M9	N.C.									Not conne	cted (not bonded	1)		
70	L9	N.C.									Not connected (not bonded)				
71	K9	P1.0/T3.OCM PB/AIN.0	I/O	pu	CT		4mA	х	х		Port 1.0	Timer 3: Output Compare B	ADC: Analog input 0		
72	L10	P1.1/T3.ICAP A/T3.EXTCLK/ AIN.1	I/O	pu	CT		4mA	x	x		Port 1.1	Timer 3: Input Capture A or External Clock input	ADC: Analog input 1		
73	M12	P1.2/T3.OCM PA/AIN.2	I/O	pu	CT		4mA	х	х		Port 1.2	Timer 3: Output Compare A	ADC: Analog input 2		
74	L11	P1.3/T3.ICAP B/AIN.3	I/O	pu	CT		4mA	х	х		Port 1.3	Timer 3: Input Capture B	ADC: Analog input 3		
75	K11	P1.4/T1.ICAP A/T1.EXTCLK	I/O	pu	CT		4mA	х	х		Port 1.4	Timer 1: Input Capture A	Timer 1: External Clock input		
76	K10	P1.5/T1.ICAP B	I/O	pu	CT		4mA	х	х		Port 1.5	Timer 1: Input Capture B			
77	J12	P1.6/T1.OCM PB	I/O	pu	CT		4mA	х	х		Port 1.6 Timer 1: Compare B				
78	J11	D.5	I/O	6)			8mA								
79	L12	D.6	I/O	6)			8mA								
80	K12	D.7	I/O	6)			8mA			External Memory Interface: data bus					
81	J10	D.8	I/O	6)			8mA								
82	J9	D.9	I/O	6)			8mA								



Table 3. STR710 pin description

Pin	n°			(le	Inp	ut	Οι	utpu	t	Stdby	Main				
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	ОD	РР	Active in Sto	Main function (after reset)	Altern	ate function		
83	H12	V _{33IO-PLL}	S								Supply voltage for digital I/O circuitry and for PLL reference ⁴⁾				
84	H11	V _{SSIO-PLL}	s								Ground vo reference ⁴		O circuitry and for PLL		
85	H10	P1.7/T1.OCM PA	I/O	pu	CT		4mA	х	x		Port 1.7	Timer 1: Output Compare A			
86	H9	P1.8	I/O	pd	CT		4mA	Х	Х		Port 1.8				
87	G12	N.C.									Not conne	cted (not bonded)		
88	F12	P1.11/CANRX	I/O	pu	CT	х	4mA	х	х		Port 1.11	CAN: receive da Note: On STR7	ata input 10 and STR712 only		
89	H8	P1.12/CANTX	I/O	pu	CT		4mA	х	х		Port 1.12	CAN: Transmit data output			
90	G11	USBDP	I/O		CT						USB bidirectional data (data +). Reset state = HiZ Note: On STR710 and STR711 only This pin requires an external pull-up to V_{33} to maintain a high level.				
91	G10	USBDN	I/O		CT							ctional data (data STR710 and STF	a -). Reset state = HiZ R711 only.		
92	G9	D.10	I/O	6)			8mA								
93	G8	D.11	I/O	6)			8mA								
94	G7	D.12	I/O	6)			8mA				Extornal	emory Interface:	data bua		
95	F11	D.13	I/O	6)			8mA					emory interface.	uala bus		
96	F10	D.14	I/O	6)			8mA								
97	F9	D.15	I/O	6)			8mA								
98	F8	A.0	0	7)			8mA		х						
99	E12	A.1	0	7)			8mA		Х						
100	E11	A.2	0	7)			8mA		Х		External M	emory Interface:	address bus		
101	C12	A.3	0	7)			8mA		Х						
102	B12	A.4	0	7)			8mA		Х						
103	E10	V _{SS}	S								Ground voltage for digital I/O circuitry ⁴⁾				
104	E9	V ₃₃	S								Supply voltage for digital I/O circuitry ⁴⁾				
105	D12	P1.9	I/O	pd	C_{T}		4mA	Х	Х		Port 1.9				
106	D11	P1.10/ USBCLK	I/O	pd	C/ T		4mA	х	х		Port 1.10 USB: 48 MHZ clock input				



Table 3. STR710 pin description

Pir	n n°			(1e	Inp	ut	Οι	utpu	t	Stdby	Mein				
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	ОD	РР	Active in Ste	Main function (after reset)	Alternate function			
107	D10	P1.13/HCLK/ I0.SCL	I/O	pd	CT	х	4mA	x	x		Port 1.13 HDLC: reference I2C clock clock input				
108	C11	P1.14/HRXD/ I0.SDA	I/O	pu	С _Т	x	4mA	х	x		Port 1.14	HDLC: Receive data input	I2C serial data		
109	B11	N.C.									Not conne	cted (not bonded	1)		
110	B10	N.C.									Not conne	cted (not bonded	1)		
111	C10	P1.15/HTXD	I/O	pu	C_{T}		4mA	Х	Х		Port 1.15	HDLC: Transmi	t data output		
112	A9	V _{SS}	S								Ground vo	Ground voltage for digital I/O circuitry ⁴⁾			
113	B9	V ₃₃	S								Supply vol	Supply voltage for digital I/O circuitry ⁴⁾			
114	C9	A.5	0	7)			8mA		Х						
115	D9	A.6	0	7)			8mA		Х						
116	A11	A.7	0	7)			8mA		Х						
117	A10	A.8	0	7)			8mA		Х						
118	A8	A.9	0	7)			8mA		Х		External N	lemory Interface	address bus		
119	B8	A.10	0	7)			8mA		Х						
120	C8	A.11	0	7)			8mA		Х						
121	A12	A.12	0	7)			8mA		Х						
122	D8	A.13	0	7)			8mA		Х						
		P0.0/S0.MISO										SPI0 Master in/Slave out data	UART3 Transmit data output		
123	E8	/U3.TX	I/O	pu	C _T		4mA	Х	Х		Port 0.0 Note: Programming AF function selects UART by default. BSPI must be enabled by SPI_EN bit in the BOOTCR register.				
		P0.1/S0.MOSI									BSPI0: Master out/Slave in data				
124	B7	/U3.RX	I/O	pu	CT	Х	4mA	Х	х		Port 0.1	Port 0.1 Note: Programming AF function selects UART by default. BSPI must be enabled by SPI_EN bit in the BOOTCR register.			



Pin	n°	-		1) ا	Inp	ut	Οι	utpu	t	Stdby	N a i a		
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	OD	dd	Active in Ste	Main function (after reset)	Altern	ate function
												BSPI0: Serial Clock	I2C1: Serial clock
125	A7	P0.2/S0.SCLK /I1.SCL	I/O	pu	C _T	х	4mA	х	х		Port 0.2		
		P0.3/S0. <u>SS</u> /										SPI0: Slave Select input active low.	I2C1: Serial Data
126	A6	I1.SDA	I/O	pu	CT		4mA	Х	Х		Port 0.3		
127	C7	P0.4/S1.MISO	I/O	pu	C_T		4mA	Х	Х		Port 0.4	SPI1: Master in	/Slave out data
128	D7	V _{SS18}	S								Stabilizatio	on for main voltag	e regulator.
129	E7	V ₁₈	S								external ca	on for main voltag apacitors of at lea ₁₈ and V _{SS18} . Se	
130	F7	A.14	0	7)			8mA		Х				
131	B6	A.15	0	7)			8mA		Х				
132	C6	A.16	0	7)			8mA		Х		Extornal M	lemory Interface:	addroce bus
133	D6	A.17	0	7)			8mA		Х			lemory intendce.	address bus
134	E6	A.18	0	7)			8mA		Х				
135	A5	A.19	0	7)			8mA		Х				
136	B5	WE.1	0	5)			8mA		х		External N enable out		active low MSB write
137	C5	WE.0	0	5)			8mA		х		External N enable out	Memory Interface: active low LSB write	
138	A3	V ₃₃	S								Supply vol	tage for digital I/C	Ds ⁴⁾
139	A2	V _{SS}	S								Ground vo	Itage for digital I/	Os ⁴⁾
140	D5	P0.5/S1.MOSI	I/O	pu	C_T		4mA	Х	Х		Port 0.5	SPI1: Master ou	it/Slave In data
141	A4	P0.6/S1.SCLK	I/O	pu	C_{T}	Х	4mA	Х	Х		Port 0.6	SPI1: Serial Clo	ck
142	B4	P0.7/S1.SS	I/O	pu	C_{T}		4mA	Х	Х		Port 0.7	SPI1: Slave Sel	ect input active low

Table 3.STR710 pin description



Pin	n°			(Le	Inp	ut	Οι	utpu	t	Stdby	Main		
LQFP144	BGA144	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	аo	dd	Active in Ste	Main function (after reset)	Altern	ate function
		P0.8/U0.RX/									Port 0.8	UART0: Receive Data input	UART0: Transmit data output.
143	C4	U0.TX	I/O	pd	CT	x	4mA	Т			(half duple Output. Th	x) if programmed	d for single wire UART as Alternate Function tated except when ogress
144	В3	P0.9/U0.TX/ BOOT.0	I/O	pd	CT		4mA	х	х		Port 0.9	Select Boot Configuration input	UART0: Transmit data output

Table 3. STR710 pin description

- The Reset configuration of the I/O Ports is IPUPD (input pull-up/pull down). Refer to Table 7 on page 29. The Port bit configuration at reset is PC0=1, PC1=1, PC2=0. The port data register bit (PD) value depends on the pu/pd column which specifies whether the pull-up or pull-down is enabled at reset
- 2. In reset state, these pins configured as Input PU/PD with weak pull-up enabled. They must be configured by software as Alternate Function (see *Table 7: Port bit configuration table on page 29*) to be used by the External Memory Interface.
- In reset state, these pins configured as Input PU/PD with weak pull-down enabled to output Address 0x0000 0000 using the External Memory Interface. To access memory banks greater than 1Mbyte, they need to be configured by software as Alternate Function (see *Table 7: Port bit configuration table on* page 29).
- 4. $V_{33IO-PLL}$ and V_{33} are internally connected. $V_{SSIO-PLL}$ and V_{SS} are internally connected.
- 5. During the reset phase, these pins are in input pull-up state. When reset is released, they are configured as Output Push-Pull.
- 6. During the reset phase, these pins are in input pull-up state. When reset is released, they are configured as Hi-Z.
- 7. During the reset phase, these pins are in input pull-down state. When reset is released, they are configured as Output Push-Pull.
- 8. During the reset phase, this pin is in input floating state. When reset is released, it is configured as Output Push-Pull.





4.4 Pin description for 64-pin packages

Figure 3. STR712/STR715 LQFP64 pinout



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Figure 4. STR711 LQFP64 pinout

Table 4. STR711 BGA ball connections

	Α	В	С	D	Е	F	G	н
1	P0.10	P0.11	P0.12	P0.14	V33	JTCK	TEST	V33IO- PLL
2	P0.9	VSS	P0.13	VSS	JTMS	JTRSTn	P0.15	VSSIO- PLL
3	P0.5	P0.7	BOOTEN	JTDI	NU	STDBY	RTCXTI	СК
4	VSS18	VSS	P0.8	JTDO	AVDD	V18BKP	RSTIN	RTCXTO
5	P0.2	P0.4	V18	P0.6	P1.9	P1.0	V18	VSSBKP
6	V33	P0.1	P0.3	P1.13	USBDP	VSSIO- PLL	AVSS	VSS18
7	VSS	P0.0	P1.10	USBDN	P1.7	P1.6	P1.5	P1.1
8	P1.15	P1.14	VSS	P1.8	V33IO- PLL	P1.4	P1.3	P1.2

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	Α	В	С	D	E	F	G	н
1	P0.10	P0.11	P0.12	P0.14	V33	JTCK	TEST	V33IO- PLL
2	P0.9	VSS	P0.13	VSS	JTMS	JTRSTn	P0.15	VSSIO- PLL
3	P0.5	P0.7	BOOTEN	JTDI	NU	STDBY	RTCXTI	СК
4	VSS18	VSS	P0.8	JTDO	AVDD	V18BKP	RSTIN	RTCXTO
5	P0.2	P0.4	V18	P0.6	P1.9	P1.0	V18	VSSBKP
6	V33	P0.1	P0.3	P1.13	P1.11/ CANRX ¹⁾	VSSIO- PLL	AVSS	VSS18
7	VSS	P0.0	P1.10	P1.12/ CANTX ¹⁾	P1.7	P1.6	P1.5	P1.1
8	P1.15	P1.14	VSS	P1.8	V33IO- PLL	P1.4	P1.3	P1.2

 Table 5.
 STR712/715 BGA Ball Connections

 $^{1)}\mbox{CANTX}$ and CANRX in STR712F only, in STR715F they are general purpose I/Os.

Legend / abbreviations for Table 6:

Туре:	I = input, O = output, S = supply, HiZ= high impedance,
In/Output level: Port and contro	C = CMOS $0.3V_{DD}/0.7V_{DD}$ C _T = CMOS $0.8V / 2V$ with input trigger T _T = TTL $0.3V/0.7V_{DD}$ with input trigger C/T = Programmable levels: CMOS $0.3V_{DD}/0.7V_{DD}$ or TTL $0.8V / 2V$ I configuration:
Input:	pu/pd= software enabled internal pull-up or pull down pu= in reset state, the internal $100k\Omega$ weak pull-up is enabled. pd = in reset state, the internal $100k\Omega$ weak pull-down is enabled.
Output:	OD = open drain (logic level) PP = push-pull T = true OD, (P-Buffer and protection diode to V_{DD} not implemented),
5V tolerant.	



Pin	n n°			(1	Inp	ut	Ou	Itpu	t	dby	Main		
LQFP64	BGA64	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	ao	dd	Active in Stdby	Main function (after reset)	Alterr	nate function
												UART1: Receive Data input	UART1: Transmit data output.
1	A1	P0.10/U1.RX/ U1.TX/ SC.DATA	I/O	pd	CT	х	4mA	Т			Port 0.10	wire UART (half as Alternate Fur	In/DataOut or single duplex) if programmed action Output. The pin except when UART
2	B1	P0.11/BOOT.1 /U1.TX	I/O	pd	CT		4mA	Х	Х		Port 0.11	Select Boot Configuration input	UART1: Transmit data output.
3	C1	P0.12/SC.CLK	I/O	pd	C_T		4mA	Х	Х		Port 0.12	Smartcard reference	ence clock output
4	B2	V _{SS}	S								Ground vo	ltage for digital I/	Os ²⁾
5	C2	P0.13/U2.RX/ T2.OCMPA	I/O	pu	CT	х	4mA	х	х		Port 0.13	UART2: Receive Data input	Timer2: Output Compare A output
6	D1	P0.14/U2.TX/ T2.ICAPA	I/O	pu	CT		4mA	х	х		Port 0.14	UART2: Transmit data output	Timer2: Input Capture A input
7	C3	BOOTEN	I		CT						Boot contr pins	ol input. Enables	sampling of BOOT[1:0]
8	D2	V _{SS}	s								Ground vo	ltage for digital I/	Os ²⁾
9	E1	V ₃₃	S								Supply vo	tage for digital I/0	Ds ²⁾
10	D3	JTDI	Ι		Τ _Τ						JTAG Data	a input. External (oull-up required.
11	E2	JTMS	I		Τ _Τ						JTAG Moc required.	le Selection Input	t. External pull-up
12	F1	JTCK	I		С						JTAG Cloo required.	k Input. External	pull-up or pull-down
13	D4	JTDO	0				8mA		Х		JTAG Data	a output. Note: R	eset state = HiZ.
14	F2	JTRST	I		Τ _Τ						JTAG Res	et Input. External	pull-up required.
15	E3	NU									Reserved	must be forced t	o ground.
16	G1	TEST									Reserved,	must be forced t	o ground.
17	H1	V _{33IO-PLL}	S								Supply vo		D circuitry and for PLL
18	H2	V _{SSIO-PLL}	S								Ground vo		O circuitry and for PLL
19	НЗ	СК	Ι		С						Reference	clock input	

 Table 6.
 STR711/STR712/STR715 pin description



Pin	n°			1)	Inp	ut	Ou	Itput	t	lby			
LQFP64	BGA64	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	QD	dd	Active in Stdby	Main function (after reset)	Altern	ate function
20	G2	P0.15/	1		Τ _Τ	х				х	Port 0.15	Wakeup from St	andby mode input.
20	5	WAKEUP			• 1	~				~	Note: This	s port is input only	/.
21	G3	RTCXTI									Realtime (amplifier c	•	put of 32 kHz oscillator
22	H4	RTCXTO									Output of	32 kHz oscillator	amplifier circuit
23	F3	STDBY	I/O		CT		4mA	x		x	low. Caution: normal mo Output: St Software S Note: In S	External pull-up to ode. andby mode activ Standby mode en tandby mode all p	•
24	G4	RSTIN	I		C_T					Х	Reset inpu	ut	
25	H5	V _{SSBKP}			S					Х	Stabilizatio	on for low power v	voltage regulator.
26	F4	V _{18BKP}			S					х	Requires of between \ Note: If the second se	e low power volta this pin can be co	′s of at least 1µF _{BKP} See <i>Figure 5</i> .
27	G5	V ₁₈	S								external c	on for main voltag apacitors of at lea / ₁₈ and V _{SS18} . Se	
28	H6	V _{SS18}	S								Stabilizatio	on for main voltag	je regulator.
29	E4	V _{DDA}	S								Supply vo	Itage for A/D Con	verter
30	G6	V _{SSA}	S								Ground vo	oltage for A/D Cor	nverter
31	F5	P1.0/T3.OCM PB/AIN.0	I/O	pu	CT		4mA	х	х		Port 1.0	Timer 3: Output Compare B	ADC: Analog input 0
32	H7	P1.1/T3.ICAP A/T3.EXTCLK /AIN.1	I/O	pu	CT		4mA	х	х		Port 1.1	Timer 3: Input Capture A or External Clock input	ADC: Analog input 1
33	H8	P1.2/T3.OCM PA/AIN.2	I/O	pu	C _T		4mA	х	Х		Port 1.2	Timer 3: Output Compare A	ADC: Analog input 2
34	G8	P1.3/T3.ICAP B/AIN.3	I/O	pu	C _T		4mA	х	х		Port 1.3	Timer 3: Input Capture B	ADC: Analog input 3
35	F8	P1.4/T1.ICAP A/T1.EXTCLK	I/O	pu	CT		4mA	х	х		Port 1.4	Timer 1: Input Capture A	Timer 1: External Clock input

Table 6. STR711/STR712/STR715 pin description



Pir	n n°			(1	Inp	ut	Ou	Itput	t	dby			
LQFP64	BGA64	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	QD	РР	Active in Stdby	Main function (after reset)	Alterr	nate function
36	G7	P1.5/T1.ICAP B	I/O	pu	C _T		4mA	х	х		Port 1.5	Timer 1: Input Capture B	
37	F7	P1.6/T1.OCM PB	I/O	pu	CT		4mA	х	х		Port 1.6	Timer 1: Output Compare B	
38	E8	V _{33IO-PLL}	S								Supply vo		O circuitry and for PLL
39	F6	V _{SSIO-PLL}	S								Ground vo	bltage for digital I/ 2)	O circuitry and for PLL
40	E7	P1.7/T1.OCM PA	I/O	pu	CT		4mA	х	х		Port 1.7	Timer 1: Output Compare A	
41	D8	P1.8	I/O	pd	C_T		4mA	Х	Х		Port 1.8		
42	E6	P1.11/CANRX	I/O	pu	CT	х	4mA	х	х		Port 1.11	CAN: receive da Note: On STR7	ta input 10 and STR712 only
43	D7	P1.12/CANTX	I/O	pu	CT		4mA	х	х		Port 1.12	CAN: Transmit d Note: On STR7	ata output 10 and STR712 only
42	E6	USBDP	I/O		C _T						Note: On This pin re	STR710 and STF	a +). Reset state = HiZ R711 only al pull-up to V ₃₃ to
43	D7	USBDN	I/O		CT							ectional data (data STR710 and STF	a -). Reset state = HiZ R711 only.
44	C8	V _{SS}	S								Ground vo	oltage for digital I/	O circuitry ²⁾
45	E5	P1.9	I/O	pd	C _T		4mA	Х	Х		Port 1.9		
46	C7	P1.10/USBCL K	I/O	pd	C/ T		4mA	х	х		Port 1.10	USB: 48 MHZ clock input	
47	D6	P1.13/HCLK/I 0.SCL	I/O	pd	С _Т	х	4mA	х	х		Port 1.13	HDLC: reference clock input	I2C clock
48	B8	P1.14/HRXD/I 0.SDA	I/O	pu	CT	х	4mA	х	х		Port 1.14	HDLC: Receive data input	I2C serial data
49	A8	P1.15/HTXD	I/O	pu	CT		4mA	Х	Х		Port 1.15	HDLC: Transmit	data output
50	A7	V _{SS}	S								Ground vo	oltage for digital I/	O circuitry ²⁾
51	A6	V ₃₃	S								Supply vo	Itage for digital I/C	D circuitry ²⁾

 Table 6.
 STR711/STR712/STR715 pin description



Pin	n°			1)	Inp	ut	Οι	Itpu	t	dby			
LQFP64	BGA64	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	ao	dd	Active in Stdby	Main function (after reset)	Alterr	nate function
		P0.0/S0.MISO										SPI0 Master in/Slave out data	UART3 Transmit data output
52	B7	/U3.TX	I/O	pu	CT		4mA	Х	х		Port 0.0	UART by default	ning AF function selects a BSPI must be EN bit in the BOOTCR
		P0.1/S0.MOSI										BSPI0: Master out/Slave in data	UART3: Receive Data input
53	B6	/U3.RX	I/O	pu	CT	х	4mA	Х	Х		Port 0.1	UART by default	ning AF function selects a BSPI must be EN bit in the BOOTCR
												BSPI0: Serial Clock	I2C1: Serial clock
54	A5	P0.2/S0.SCLK /I1.SCL	I/O	pu	CT	х	4mA	Х	х		Port 0.2	I2C by default. E	hing AF function selects SPI must be enabled the BOOTCR register.
55	C6	P0.3/S0. <u>SS</u> /I1	I/O	~	0		4	х	x		Port 0.3	SPI0: Slave Select input active low.	I2C1: Serial Data
55	6	.SDA	1/0	pu	CT		4mA	Χ	~		Port 0.3	I2C by default. E	hing AF function selects SPI must be enabled the BOOTCR register.
56	B5	P0.4/S1.MISO	I/O	pu	C_T		4mA	Х	Х		Port 0.4	SPI1: Master in/	Slave out data
57	A4	V _{SS18}	S								Stabilizati	on for main voltag	ge regulator.
58	C5	V ₁₈	S								external c	on for main voltag apacitors of at lea / ₁₈ and V _{SS18} . Se	
59	B4	V _{SS}	S								Ground vo	oltage for digital I/	Os
60	A3	P0.5/S1.MOSI	I/O	pu	C_T		4mA	Х	Х		Port 0.5	SPI1: Master ou	t/Slave In data
61	D5	P0.6/S1.SCLK	I/O	pu	C_{T}	Х	4mA	Х	Х		Port 0.6	SPI1: Serial Clo	ck
62	B3	P0.7/S1.SS	I/O	pu	CT		4mA	Х	Х		Port 0.7	SPI1: Slave Sele	ect input active low

Table 6. STR711/STR712/STR715 pin description



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		01117-0											
Pin	n°			(1e	Inp	ut	Οι	Itput	t	Stdby	Main		
LQFP64	BGA64	Pin Name	Type	Reset State ¹⁾	Input Level	interrupt	Capability	ao	dd	Active in St	function (after reset)	Altern	ate function
		P0.8/U0.RX/U									Port 0.8	UART0: Receive Data input	UART0: Transmit data output.
63	C4	0.TX	I/O	pd	C _T	х	4mA	Т			(half duple Output. Th	ex) if programmed	d for single wire UART I as Alternate Function tated except when ogress
64	A2	P0.9/U0.TX/B OOT.0	I/O	pd	CT		4mA	х	Х		Port 0.9	Select Boot Configuration input	UART0: Transmit data output

Table 6. STR711/STR712/STR715 pin description

 The Reset configuration of the I/O Ports is IPUPD (input pull-up/pull down). Refer to *Table 7 on page 29*. The Port bit configuration at reset is PC0=1, PC1=1, PC2=0. The port data register bit (PD) value depends on the pu/pd column which specifies whether the pull-up or pull-down is enabled at reset

2. $V_{\rm 33IO\text{-}PLL}$ and $V_{\rm 33}$ are internally connected. $V_{\rm SSIO\text{-}PLL}$ and $V_{\rm SS}$ are internally connected.

4.5 External connections





4.6 I/O port configuration

Table 7. Port bit configuration table

	Configuration Mode	Input		¢D ister	PxC2	PxC1	PxC0
		Buffer	Read access	Write access	Register	Register	Register
	TTL Input Floating	TTL floating	I/O pin	don't care	0	0	1
	CMOS Input Floating	CMOS floating	I/O pin	don't care	0	1	0
INPUT	CMOS Input Pull-Down (IPUPD)	CMOS Pull- Down	I/O pin	0	0	1	1
	CMOS Input Pull-Up (IPUPD)	CMOS Pull-Up	I/O pin	1	0	1	1
	Analog input	AIN	0	don't care	0	0	0
	Output Open-Drain	N.A.	I/O pin	0 or 1	1	0	0
OUTPUT	Output Push-Pull	N.A.	last value written	0 or 1	1	0	1
	Alternate Function Open-Drain	CMOS floating	I/O pin	don't care	1	1	0
	Alternate Function Push-Pull	CMOS floating	I/O pin	don't care	1	1	1

Legend:

AIN: Analog Input

CMOS: CMOS Input levels

IPUPD: Input Pull Up /Pull Down

TTL: TTL Input levels

N.A.: not applicable. In Output mode, a read access to the port gets the output latch value.

4.7 Memory mapping







	Memory Space + 16K RWW + I			Memory Space + 16K RWW +			Memory Space + 16K RWW +	
0x4010 DFBF 0x4010 0000	FLASH Registers	36b	0x4010 DFBF 0x4010 0000	FLASH Registers	36b	0x4010 DFBF 0x4010 0000	FLASH Registers	30
	reserved		0.1010 0000	reserved	1	0,1010 0000	reserved	
0x400C 4000			0x400C 4000			0x400C 4000		
	B1F1	8K		B1F1	8К		B1F1	8
0x400C 2000			0x400C 2000			0x400C 2000		
0x400C 0000	B1F0	8K	0x400C 0000	B1F0	8K	0x400C 0000	B1F0	8
0.1000 0000			0.11000 0000					
	reserved			reserved	1		reserved	
0x4004 0000			0x4004 0000			0x4004 0000		
	reserved	64K		reserved	64K		B0F7	6
0x4003 0000		-	0x4003 0000			0x4003 0000		
	reserved	64K		reserved	64K		B0F6	6
0x4002 0000			0x4002 0000			0x4002 0000		
	reserved	64K		B0F5	64K		B0F5	6
0x4001 0000			0x4001 0000			0x4001 0000		
	B0F4	32K		B0F4	32K		B0F4	3
0x4000 8000 0x4000 6000	B0F3	8К	0x4000 8000 0x4000 6000	B0F3	8К	0x4000 8000 0x4000 6000	B0F3	8
0x4000 8000 0x4000 4000	B0F2	8K	0x4000 8000 0x4000 4000	B0F2	8K	0x4000 4000	B0F2	8
0x4000 2000 0x4000 0000	B0F1 B0F0	8K 8K	0x4000 2000 0x4000 0000	B0F1 B0F0	8K 8K	0x4000 2000 0x4000 0000	B0F1 B0F0	8

Figure 7. Mapping of Flash memory versions

Table 8.RAM memory mapping

Part Number	RAM Size	Start Address	End Address
STR715FR0xx STR711FR0xx STR712FR0xx	16 Kbytes	0x2000 0000	0x2000 3FFF
STR710FZ1xx STR711FR1xx STR712FR1xx	32 Kbytes	0x2000 0000	0x2000 7FFF
STR710FR2xx STR710Rxx STR711FR2xx STR712FR2xx	64 Kbytes	0x2000 0000	0x2000 FFFF





Figure 8. External memory map



5 Electrical parameters

5.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A=25$ °C and $T_A=T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\Sigma$).

5.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A=25^{\circ}C$, $V_{33}=3.3V$ (for the $3.0V \le V_{33} \le 3.6V$ voltage range) and $V_{18}=1.8V$. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\Sigma$).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 9.

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 10*.Figure 9.Pin loading conditionsFigure 10.Pin loading conditionsFigure 10.





5.2 Absolute maximum ratings

Stresses above those listed as "absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Мах	Unit	
V ₃₃ - V _{SS}	External 3.3V Supply voltage (including AV_{DD} and V_{33IO} . PLL) ²⁾	-0.3	4.0		
V _{18BKP} - V _{SSBKP}	Digital 1.8V Supply voltage on V_{18BKP} backup supply ²⁾	-0.3	2.0		
V _{IN}	Input voltage on true open drain pin (P0.10) ¹⁾	V _{ss} -0.3	+5.5		
↓ IN	Input voltage on any other pin ¹⁾	V _{ss} -0.3	V ₃₃ +0.3		
l∆V _{33x} l	$ \Delta V_{33x} $ Variations between different 3.3V power pins50 $ \Delta V_{18x} $ Variations between different 1.8V power pins 5)25		50		
l∆V _{18x} l			25	mV	
IV _{SSX} - V _{SS} I	Variations between all the different ground pins	50	50		
V _{ESD(HBM)}	Electro-static discharge voltage (Human Body Model)	see : Absolute Maximum Ratings			
V _{ESD(MM)}	Electro-static discharge (Electrical Sensitivity) on page 48 voltage (Machine Model)				

Table 9. Voltage characteristics



Symbol	Symbol Ratings		Unit
I _{V33}	Total current into $V_{33}/V_{33IO-PLL}$ power lines (source) ²⁾	150	
I _{VSS}	Total current out of $V_{SS}/V_{SSIO-PLL}$ ground lines (sink) ²⁾	150	
l	Output current sunk by any I/O and control pin	25	
Ι _{ΙΟ}	Output current source by any I/Os and control pin	- 25	mA
	Injected current on RSTIN pin	± 5	ША
I _{INJ(PIN)} 1) & 3)	Injected current on CK pin	± 5	
	Injected current on any other pin 4)	± 5	
ΣΙ _{INJ(PIN)} 1)	INJ(PIN) ¹⁾ Total injected current (sum of all I/O and control pins) ⁴⁾		

Table 10. Current characteristics

Notes:

- 1. I_{INJ(PIN)} must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the I_{INJ(PIN)} value. A positive injection is induced by V_{IN}>V₃₃ while a negative injection is induced by V_{IN}<V_{SS}. For true open-drain pads, there is no positive injection current, and the corresponding V_{IN} maximum must always be respected
- 2. All 3.3V power (V₃₃, AV_{DD}, V_{33IO-PLL}) and ground (V_{SS}, AV_{SS}, V_{SSIO-PLL}) pins must always be connected to the external 3.3V supply.
- 3. Negative injection disturbs the analog performance of the device. See note in *Section 5.3.9: ADC characteristics on page 65.*
- 4. When several inputs are submitted to a current injection, the maximum Σl_{INJ(PIN)} is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with Σl_{INJ(PIN)} maximum current injection on four I/O port pins of the device.
- Only when using external 1.8V power supply. All the power (V₁₈, V_{18BKP}) and ground (V_{SS18}, V_{SSBKP}) pins must always be connected to the external 1.8V supply.

Table 11.Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-65 to +150	°C
TJ	Maximum junction temperature (see Section 6.2: Thermal characteristics of page 71)		



5.3 Operating conditions

Subject to general operating conditions for $V_{33}\text{,}$ and $T_{A}\text{.}$

Symbol	Parameter	Conditions	Min	Max	Unit	
		Accessing SRAM or external memory with 0 wait states	0	66	- MHz	
f	Internal CPU Clock frequency	Accessing FLASH in burst mode	0	50		
^f MCLK		Executing from FLASH with RWW	0	45 ¹⁾		
		Accessing FLASH with 0 wait states	0	33		
f _{PCLK}	Internal APB Clock frequency		0	33	MHz	
V ₃₃	Standard Operating Voltage (includes V _{33I0_PLL})		3.0	3.6	V	
V _{18BKP}	Backup Operating Voltage		1.4	1.8	V	
T _A	Ambient temperature range	6 Partnumber Suffix	-40	85	°C	

 Table 12.
 General Operating Conditions

1. Data guaranteed by characterization, not tested in production

Table 13. Operating Conditions at power-up / power-down

	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	t_{V33} V ₃₃ rise time rate	Subject to general	20			μs/V	
		v ₃₃ rise time rate	operating conditions for T_A .			20	ms/V


5.3.1 Supply current characteristics

The current consumption is measured as described in *Figure 9 on page 33* and *Figure 10 on page 33*.

Total current consumption

The MCU is placed under the following conditions:

- All I/O pins in input mode with a static value at V₃₃ or V_{SS} (no load)
- All peripherals are disabled except if explicitly mentioned.
- Embedded Regulators are used to provide 1.8V (except if explicitly mentioned)

Subject to general operating conditions for V_{33} , and T_A .

Table 14.	Total	Current	consumption
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Symbol	Parameter	Conditions	Typ ¹⁾	Max ²⁾	Unit
	Supply current in RUN mode	f _{MCLK} =66 MHz, RAM execution	73.6	100	
I _{DD} ⁴⁾		f _{MCLK} =32 MHz, Flash non-burst execution	49.3		mA
	Supply current in STOP mode	T _A =25°C	10	50 ³⁾	μA
	Supply current in STANDBY mode	OSC32K bypassed	12	30	μA

Notes:

- 1. Typical data are based on $T_A=25^{\circ}C$, $V_{33}=3.3V$.
- 2. Data based on characterization results, tested in production at V_{33} , f_{MCLK} max. and T_A max.
- 3. Based on device characterisation, device power consumption in STOP mode at $T_A\,25^\circ C$ is predicted to be $30\mu A$ or less in 99.730020% of parts.
- 4. The conditions for these consumption measurements are described in application note AN2100.



Symbol	Para	meter	Conditions	Typical current on V33	Unit
			MCLK = 16 MHz, PCLK = FCLK = 16 MHz	23	
			MCLK = 32 MHz, PCLK = FCLK = 32 MHz	40	
		All periphs ON	MCLK = 48 MHz, PCLK = FCLK = 24 MHz	50	
	RUN mode		MCLK = 64 MHz, PCLK = FCLK = 32 MHz	63	
	current from RAM		MCLK = 16 MHz	16	
			MCLK = 32 MHz	26	
		All periphs OFF	MCLK = 48 MHz	39	
IDDRUN			MCLK = 64 MHz	48	
			MCLK = 16 MHz, PCLK = FCLK = 16 MHz	27	mA
		All periphs ON	MCLK = 32 MHz, PCLK = FCLK = 32 MHz	47	
	RUN mode		MCLK = 48 MHz, PCLK = FCLK = 24 MHz	62	
	current from FLASH		MCLK = 16 MHz	21	
			MCLK = 32 MHz	36	
			MCLK = 48 MHz	53	
IDDSLOW	SLOW mode current		MCLK = CK_AF (32 kHz), MVR off	1.7	
I _{DDWAIT}	WAIT mode current (all periphs ON)		PCLK = FCLK = 1 MHz	13	
IDDLPWAIT	LPWAIT m	node current	CK_AF (32 kHz), Main VReg off, FLASH in power-down	37	
			Main VReg off, FLASH in power down, RTC on	18	
DDSTOP	I _{DDSTOP} STOP mode current		Main VReg off, FLASH in power down, RTC off	10	
			LP VReg on, LVD on, RTC on	10	μA
			LP VReg off (ext 1.8V on V18BKP), LVD on, RTC on	9	ĺ
I _{DDSB}	STANDBY	mode current	LP VReg off (ext1.8V on V18BKP), LVD off, RTC on	5	
			LP VReg off (ext 1.8V on V18BKP), LVD off, RTC off	1	

 Table 15.
 Typical power consumption data







Figure 12. STANDBY I_{DD} vs. V_{33}





On-Chip Peripherals

Table 16.	Peripheral	current	consumption
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Symbol	Parameter	Conditions	Тур	Unit
I _{DD(PLL1)}	PLL1 supply current	T _A = 25°C	3.42	
I _{DD(PLL2)}	PLL2 supply current	1 _A - 23 0	5.81	
I _{DD(TIM)}	TIM Timer supply current ¹⁾		0.88	
I _{DD(BSPI)}	BSPI supply current ²⁾		1.1	
I _{DD(UART)}	UART supply current ²⁾		1.05	
I _{DD(I2C)}	I2C supply current ²⁾	Т _A = 25°С, f _{PCI K} =33 MHz	0.45	mA
I _{DD(ADC)}	ADC supply current when converting ⁵⁾	r _A - 23 0, r _{PCLK} -33 m rz	1.89	
I _{DD(HDLC)}	HDLC supply current ²⁾		1.82	
I _{DD(USB)}	USB supply current ²⁾		2.08	
I _{DD(CAN)}	CAN supply current ²⁾		1.11	

Notes:

- Data based on a differential I_{DD} measurement between reset configuration and timer counter running at 16MHz. No IC/OC programmed (no I/O pads toggling).
- 2. Data based on a differential I_{DD} measurement between the on-chip peripheral when kept under reset and not clocked and the on-chip peripheral when clocked and not kept under reset. No I/O pads toggling.
- 3. Data based on a differential ${\rm I}_{\rm DD}$ measurement between reset configuration and continuous A/D conversions.



5.3.2 Clock and timing characteristics

External Clock Sources

Subject to general operating conditions for $V_{\rm 33},$ and $T_{\rm A}.$

Table 17. CK External Clock Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{CK}	External clock source frequency		0		16.5	MHz
V _{CKH}	CK input pin high level voltage		0.7xV ₃₃		V ₃₃	v
V _{CKL}	CK input pin low level voltage		V _{SS}		0.3xV ₃₃	v
t _{w(CK)} t _{w(CK)}	CK high or low time ¹⁾		25			nc
t _{r(СК)} t _{f(СК)}	CK rise or fall time ¹⁾				5	ns
١L	CK Input leakage current	$V_{SS} \leq V_{IN} \leq V_{33}$			±1	μA

Notes:

1. Data based on design simulation and/or technology characteristics, not tested in production.

Figure 14.	CK External	Clock Source
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{RTCXT1}	External clock source frequency		0		500	kHz
V _{RTCXT1H}	RTCXT1 input pin high level voltage		0.7xV ₃₃		V ₃₃	v
V _{RTCXT1L}	RTCXT1 input pin low level voltage		V _{SS}		0.3xV ₃₃	v
t _{w(RTCXT1)} t _{w(RTCXT1)}	RTCXT1 high or low time ¹⁾		100			ns
t _{r(RTCXT1)} t _{f(RTCXT1)}	RTCXT1 rise or fall time ¹⁾				5	115
۱ _L	RTCXT1 Input leakage current	$V_{SS} \leq V_{IN} \leq V_{33}$			±1	μA

Table 18. RTCXT1 External Clock Characteristics

Notes:

1. Data based on design simulation and/or technology characteristics, not tested in production.



OSC32K crystal / Ceramic resonator oscillator

The STR7 RTC clock can be supplied with a 32kHz Crystal/Ceramic resonator oscillators. All the information given in this paragraph are based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

Symbol	Parameter	Conditions	Тур	Unit
R _F	Feedback resistor		2.7	MΩ
C _{L1} C _{L2}	Recommended load capacitance versus equivalent serial resistance of the crystal (R _S) ¹⁾	R _S =40KΩ	12.5	pF
i ₂	RTCXT2 driving current	V ₃₃ =3.3V V _{IN} =V _{SS}	3.2	μA
9 _m	Oscillator Transconductance		8	μA/V
t _{SU(OSC32KHZ)} ²⁾	startup time	V_{33} is stabilized	5	S

Table 19. 32K Oscillator characteristics (f_{OSC32K=} 32.768kHz)

Notes:

- 1. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details
- t_{SU/OSC32KHZ} is the start-up time measured from the moment it is enabled (by software) to a stabilized 32kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer









PLL electrical characteristics

 V_{33} = 3.0 to 3.6V, $V_{33IOPLL}$ = 3.0 to 3.6V, T_A = -40 / 85 $^\circ C$ unless otherwise specified.

Cumhal	Devenuetev	Task Canditiana	Value			Unit
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
f _{PLLCLK1}	PLL multiplier output clock	f _{PLL1} x 24			165	MHz
		FREF_RANGE = 0	1.5		3.0	MHz
		FREF_RANGE = 1	3.0		8.25	MHz
f _{PLL1}	PLL input clock	MX[1:0]='00' or '01'				
		FREF_RANGE = 1	3.0		6	MHz
		MX[1:0]='10' or '11'			-	
	PLL input clock duty cycle		25		75	%
	PLL free running frequency	FREF_RANGE = 0		125		kHz
		MX[1:0]='01' or '11'				KI IZ
		FREF_RANGE = 0		250		kHz
f		MX[1:0]='00' or '10'		250		KIIZ
f _{FREE1}		FREF_RANGE = 1		250		kHz
		MX[1:0]='01' or '11'		250		KI IZ
		FREF_RANGE = 1		500		kHz
l		MX[1:0]='00' or '10'		500		KI IZ
+	PLL lock time	FREF_RANGE = 0 Stable Input Clock Stable V _{33IOPLL} , V ₁₈			300	μs
t _{LOCK1}		FREF_RANGE = 1 Stable Input Clock Stable V _{33IOPLL} , V ₁₈			600	μs
$\Delta t_{\text{JITTER1}}$	PLL jitter (peak to peak)	t _{PLL} = 4 MHz, MX[1:0]='11' Global Output division = 32 (Output Clock = 2 MHz)		0.7	2	ns

Table 20. PLL1 characteristics



Symbol	Parameter	Test Conditions	Value			Unit
Symbol	Falametei	Test Conditions	Min	Тур	Max	Offic
f _{PLLCLK2}	PLL multiplier output clock	f _{PLL} x 28			140	MHz
f	f DLL input clock	FREF_RANGE = 0	1.5		3.0	MHz
f _{PLL2}	PLL input clock	FREF_RANGE = 1	3.0		5	MHz
t _{LOCK2}	PLL lock time	FREF_RANGE = 0 Stable Input Clock Stable $V_{33IOPLL}$, V_{18}			300	μs
		FREF_RANGE = 1 Stable Input Clock Stable $V_{33IOPLL}$, V_{18}			600	μs
$\Delta t_{\text{JITTER2}}$	PLL jitter (peak to peak)	t _{PLL} = 4 MHz, MX[1:0]='11' Global Output division = 32 (Output Clock = 2 MHz)		0.7	2	ns

Table 21. PLL2 characteristics

Table 22. Low-power mode wake-up timing

Symbol	Parameter	Тур	Unit
t _{WULPWFI}	Wake-up from LPWFI mode	26 ⁽¹⁾	μs
t _{WUSTOP}	Wake-up from STOP mode	2048	CLK Cycles
t _{WUSTBY}	Wake-up from STANDBY mode	2048 CLK Cycles + 8 CLK2 Cycles ⁽²⁾	Cycles

1. Clock selected is CK2_16, Main VReg OFF and Flash in power-down

2. Refer to Figure 7. Reset General Timing in the STR71xF Reference Manual (UM0084)



5.3.3 Memory characteristics

Flash memory

 V_{33} = 3.0 to 3.6V, T_A = -40 to 85 $^\circ C$ unless otherwise specified.

Table 23. Flash memory characteristi

0h.sl	Domenter	To at Oan ditions	Value			11
Symbol	Parameter	Test Conditions	Min.	Тур	Max ¹⁾	Unit
t _{PW}	Word Program			40		μs
t _{PDW}	Double Word Program			60		μs
t _{PB0}	Bank 0 Program (256K)	Double Word Program		1.6	2.1	S
t _{PB1}	Bank 1 Program (16K)	Double Word Program		130	170	ms
t _{ES}	Sector Erase (64K)	Not preprogrammed Preprogrammed		2.3 1.9	4.0 3.3	s
t _{ES}	Sector Erase (8K)	Not preprogrammed Preprogrammed		0.7 0.6	1.1 1.0	s
t _{ES}	Bank 0 Erase (256K)	Not preprogrammed Preprogrammed		8.0 6.6	13.7 11.2	s
t _{ES}	Bank 1 Erase (16K)	Not preprogrammed Preprogrammed		0.9 0.8	1.5 1.3	s
t _{RPD} ²⁾	Recovery when disabled				20	μs
t _{PSL} 2)	Program Suspend Latency				10	μs
t _{ESL} 2)	Erase Suspend Latency				300	μs
N _{END_B0}	Endurance (Bank 0 sectors)		10			kcycles
N _{END_B1}	Endurance (Bank 1 sectors)		100			kcycles
t _{RET}	Data Retention (Bank 0 and Bank 1)	T _A =85°	20			Years
t _{ESR}	Erase Suspend Rate	Min time from Erase Resume to next Erase Suspend	20			ms

Notes:

1. $T_A\!=\!45^\circ\!C$ after 0 cycles. Guaranteed by characterization, not tested in production.

2. Guaranteed by design, not tested in production



5.3.4 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (Electro Magnetic Susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electro magnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electro-Static Discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

In the case of an ARM7 CPU, in order to write robust code that can withstand all kinds of stress, such as very strong electromagnetic disturbance, it is mandatory that the Data Abort, Prefetch Abort and Undefined Instruction exceptions are managed by the application software. This will prevent the code going into an undefined state or performing any unexpected operation.



Symbol	Parameter	Conditions	Level/ Class		
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V ₃₃ =3.3V, T _A =+25°C, f _{MCLK} =32MHz conforms to IEC 1000-4-2	2B		
V _{EFTB}	Fast transient voltage burst limits to be applied through 100pF on $V_{\rm DD}$ and $V_{\rm SS}$ pins to induce a functional disturbance	V ₃₃ =3.3V, T _A =+25°C, f _{MCLK} =32MHz conforms to IEC 1000-4-4	4A		

Table 24. EMS data

Electro Magnetic Interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 25.	EMI data
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Symbol	Parameter Conditions		Monitored	Max [f _{OSC4N}	Unit	
	Farameter	Conditions	Frequency Band	16/ 48MHz	16/8MHz	Omt
	S _{EMI} Peak level V ₃₃ =3.3V, T _A =+25°C, LQFP64 package conforming to SAE J 1752/3	0.1MHz to 30 MHz	17	19		
S		LQFP64 package conforming to SAE J	30 MHz to 130 MHz	17	16	$dB\mu V$
GEWI			130 MHz to 1GHz	11	11	
			SAE EMI Level	4	3	-

Notes:

1. Not tested in production.

2. BGA and LQFP devices have similar EMI characteristics.

Absolute Maximum Ratings (Electrical Sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electro-Static Discharge (ESD)

Electro-Static Discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: Human Body Model and Machine Model. This test conforms to the JESD22-A114A/A115A standard.



Symbol	Ratings	Conditions	Maximum value ¹⁾	Unit
V _{ESD(HBM)}	Electro-static discharge voltage (Human Body Model)		2000	
V _{ESD(MM)}	Electro-static discharge voltage (Machine Model)	T _A =+25°C	200	v
V _{ESD(CDM)}	Electro-static discharge voltage		750 on corner pins, 500 on others	

Table 26. ESD Absolute Maximum ratings

Notes:

1. Data based on characterization results, not tested in production.

Static and Dynamic Latch-Up

- LU: 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.
- **DLU**: Electro-Static Discharges (one positive then one negative test) are applied to each pin of 3 samples when the micro is running to assess the latch-up performance in dynamic mode. Power supplies are set to the typical values, the oscillator is connected as near as possible to the pins of the micro and the component is put in reset mode. This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details, refer to the application note AN1181.

Electrical Sensitivities

Symbol	Parameter	Conditions	Class ¹⁾
LU	Static latch-up class	$T_{A}=+25^{\circ}C$ $T_{A}=+85^{\circ}C$ $T_{A}=+105^{\circ}C$	A A A
DLU	Dynamic latch-up class	V_{DD} =3.3V, f _{OSC4M} =4MHz, f _{MCLK} =32MHz, T _A =+25°C	А

Notes:

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).



5.3.5 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{33} and T_A unless otherwise specified. All unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	Input low level voltage 1)				0.3V ₃₃	V
V _{IH}	Input high level voltage 1)	CMOS ports	0.7V ₃₃			v
V _{hys}	Schmitt trigger voltage hysteresis 2)			0.8		V
V _{IL}	Input low level voltage 1)			0.9	0.8	V
V _{IH}	Input high level voltage 1)	P0.15 WAKEUP	2	1.35		v
V _{hys}	Schmitt trigger voltage hysteresis 2)			0.4		V
V _{IL}	Input low level voltage 1)	TTL ports			0.8	v
V _{IH}	Input high level voltage 1)	TTE ports	2.0			v
I _{INJ(PIN)}	Injected Current on any I/O pin				± 4	
ΣI _{INJ(PIN)} 3)	Total injected current (sum of all I/O and control pins)				± 25	mA
I _{lkg}	Input leakage current 4)	$V_{SS} \leq V_{IN} \leq V_{33}$			±1	μA
R _{PU}	Weak pull-up equivalent resistor ⁵⁾	V _{IN} =V _{SS}	110	150	700	kΩ
R _{PD}	Weak pull-down equivalent resistor ⁵⁾	V _{IN} =V ₃₃	110	150	700	kΩ
C _{IO}	I/O pin capacitance			5		pF

Table 27. I/O static characteristics

Notes:

- 1. Data based on characterization results, not tested in production.
- 2. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested.

3. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to I_{INJ(PIN)} specification. A positive injection is induced by V_{IN}>V₃₃ while a negative injection is induced by V_{IN}<V_{SS}. Refer to *Section 5.2 on page 34* for more details.

- 4. Leakage could be higher than max. if negative current is injected on adjacent pins.
- The R_{PU} pull-up and R_{PD} pull-down equivalent resistor are based on a resistive transistor (corresponding I_{PU} and I_{PD} current characteristics described in *Figure 18* to *Figure 19*).





Figure 17. R_{PU} vs. V_{33} with $V_{IN}=V_{SS}$



Figure 19. R_{PD} vs. V_{33} with $V_{IN}=V_{33}$



Output driving current

Subject to general operating conditions for $V_{33}\,\text{and}\,\,T_A$ unless otherwise specified.

l/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
dard	V _{OL} ¹⁾	Output low level voltage for an I/O pin when 8 pins are sunk at same time (see <i>Figure 21</i>)	I _{IO} =+4mA		0.4	
V _{OH} ²		Output high level voltage for an I/O pin when 4 pins are sourced at same time (see <i>Figure 21</i> and <i>Figure 23</i>)	I _{IO} =-4mA	V ₃₃ -0.8		v
urrent	V _{OL} ¹⁾	Output low level voltage for an I/O pin when 8 pins are sunk at same time (see <i>Figure 21</i>)	I _{IO} =+8mA		0.4	v
High Current	V _{OH} ²⁾	Output high level voltage for an I/O pin when 4 pins are sourced at same time (see <i>Figure 21</i> and <i>Figure 23</i>)	I _{IO} =-8mA	V ₃₃ -0.8		

Table 28.Output driving current

Notes:

- 1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 10* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
- 2. The I_{IQ} current sourced must always respect the absolute maximum rating specified in *Table 10* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{V33}.





Figure 21. Typical V_{OL} and V_{OH} at V₃₃=3.3V (High current ports)



STR71xF











RSTIN pin

The RSTIN pin input driver is CMOS. A permanent pull-up is present which is the same as as R_{PU} (see *Table 27 on page 50*)

Subject to general operating conditions for V_{33} and T_{A} unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ ¹⁾	Мах	Unit
V _{IL(RSTINn)}	RSTIN Input low level voltage 1)				0.8	v
V _{IH(RSTINn)}	RSTIN Input high level voltage 1)		2			v
V _{F(RSTINn)}	RSTIN Input filtered pulse ²⁾				500	ns
V _{NF(RSTINn)}	RSTIN Input not filtered pulse ²⁾		1.2			μs

Table 29. RESET pin characteristics

Notes:

- 1. Data based on characterization results, not tested in production.
- 2) Data guaranteed by design, not tested in production.

Figure 24. Recommended **RSTIN** pin protection.¹⁾



Notes:

- The R_{PU} pull-up equivalent resistor is based on a resistive transistor (corresponding I_{PU} current characteristics described in *Figure 18*).
- 2. The reset network protects the device against parasitic resets.
- The user must ensure that the level on the RSTIN pin can go below the V_{IL(RSTINn)} max. level specified in Table 29. Otherwise the reset will not be taken into account internally.

5.3.6 TIM timer characteristics

Subject to general operating conditions for V_{33} , f_{MCLK} , and T_A unless otherwise specified.

Refer to *Section 5.3.5: I/O port pin characteristics on page 50* for more details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output...).

Table 30. TIM characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{w(ICAP)} in	Input capture pulse time		2			$t_{\rm CK_TIM}$



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit		
t ann	Timer resolution time		1			t _{PCLK2}		
^t res(TIM)		f _{PCLK2} = 30MHz	33.3			ns		
f _{EXT}	Timer external clock frequency	f _{CK_TIM(MAX)} = f _{MCLK}	0		f _{CK_TIM} /4	MHz		
'EXT		f _{CK_TIM} = f _{MCLK} = 60MHz	0		15	MHz		
Res _{TIM}	Timer resolution				16	bit		
+	16-bit Counter clock period		1		65536	t _{PCLK}		
^t COUNTER	when internal clock is selected	f _{PCLK2} = 30MHz	0.033		2184	μs		
T _{MAX_COUNT}	T Maximum Possible Count				65536x 65536	t _{PCLK}		
		f _{PCLK2} = 30MHz			143.1	S		

Table 30.TIM characteristics

5.3.7 EMI - External Memory Interface

Subject to general operating conditions for $V_{\text{DD}},\,f_{\text{HCLK}},$ and T_{A} unless otherwise specified.

The tables below use a variable which is derived from the EMI_BCONn registers (described in the STR71x Reference Manual) and represents the special characteristics of the programmed memory cycle.

Table 31.	EMI general characteristics
-----------	-----------------------------

Symbol	Parameter	Value
t _{MCLK}	CPU clock period	1 / f _{MCLK}
t _C	Memory cycle time wait states	t _{MCLK} x (1 + [C_LENGTH])

Symbol	Parameter	Test Conditions	Min ¹⁾	Тур	Max ¹⁾	Unit
t _{RCR}	Read to CSn Removal Time		19	t _{MCLK}	21	ns
t _{RP}	Read Pulse Time	-	98	t _C	100	ns
t _{RDS}	Read Data Setup Time		22			ns
t _{RDH}	Read Data Hold Time	MCLK=50 MHz	0			ns
t _{RAS}	Read Address Setup Time	4 wait states 50 pf load on all pins	27	1.5*t _M CLK	33	ns
t _{RAH}	Read Address Hold Time		0.65		2	ns
t _{RAT}	Read Address Turnaround Time		1.9		3.25	ns
t _{RRT}	RDn Turnaround Time		20	t _{MCLK}	21	ns

Table 32. EMI Read Operation

See Figure 25, Figure 26, Figure 27 and Figure 28 for related timing diagrams.

1. Data based on characterisation results, not tested in production.

Table 33.	EMI Write Operation	

Cumbal	Deveneder	Test Canditions		Unit		
Symbol	Parameter	Test Conditions	Min ¹⁾	Тур	Max ¹⁾	Unit
t _{WCR}	WEn to CSn Removal Time		20	t _{MCLK}	22.5	ns
t _{WP}	Write Pulse Time		77.5	t _C	80	ns
t _{WDS1}	Write Data Setup Time 1		97	t _C + t _{MCLK}	100	ns
t _{WDS2}	Write Data Setup Time 2	MCLK=50 MHz	77	t _C	80	ns
t _{WDH}	Write Data Hold Time	3 wait states	20	t _{MCLK}	23	ns
t _{WAS}	Write Address Setup Time	50 pf load on all pins	27	1.5*t _{MCLK}	33	ns
t _{WAH}	Write Address Hold Time		0.6		3	ns
t _{WAT}	Write Address Turnaround Time		1.75		4.1	ns
t _{WWT}	WEn Turnaround Time		20	t _{MCLK}	23	ns

See Figure 29, Figure 30, Figure 31 and Figure 32 for related timing diagrams.

1. Data based on characterisation results, not tested in production.





Figure 25. Read Cycle Timing: 16-bit READ on 16-bit Memory





See Table 32 for read timing data.

Figure 27. Read Cycle Timing: 16-bit READ on 8-bit Memory





Figure 28. Read Cycle Timing: 32-bit READ on 8-bit Memory

See Table 32 for read timing data.



Figure 29. Write Cycle Timing: 16-bit WRITE on 16-bit Memory

Figure 30. Write Cycle Timing: 32-bit WRITE on 16-bit Memory



See Table 42 for write timing data.





Figure 31. Write Cycle Timing: 16-bit WRITE on 8-bit Memory





See *Table 33* for write timing data.



5.3.8 Communications interfaces

I²C - Inter IC Control Interface

Subject to general operating conditions for V_{33} , f_{PCLK1} , and T_A unless otherwise specified.

The STR7 I²C interface meets the requirements of the Standard I²C communication protocol described in the following table with the restriction mentioned below:

Note: **Restriction:** The I/O pins which SDA and SCL are mapped to are not "True" Open-Drain: when configured as open-drain, the PMOS connected between the I/O pin and V_{33} is disabled, but it is still present. Also, there is a protection diode between the I/O pin and V_{33} . Consequently, when using this I^2C in a multi-master network, it is not possible to power off the STR7X while some another I^2C master node remains powered on: otherwise, the STR7X will be powered by the protection diode.

Refer to I/O port characteristics for more details on the input/output alternate function characteristics (SDA and SCL).

Symbol	Symbol Parameter		rd mode C	Fast mo	de l ² C ⁵⁾	Unit
		Min ¹⁾	Max ¹⁾	Min ¹⁾	Max ¹⁾	
t _{w(SCLL)}	SCL clock low time	4.7		1.3		
t _{w(SCLH)}	SCL clock high time	4.0		0.6		μs
t _{su(SDA)}	SDA setup time	250		100		
t _{h(SDA)}	SDA data hold time	0 ³⁾		0 ²⁾	900 ³⁾	
t _{r(SDA)} t _{r(SCL)}	SDA and SCL rise time		1000	20+0.1C b	300	ns
t _{f(SDA)} t _{f(SCL)}	SDA and SCL fall time		300	20+0.1C b	300	
t _{h(STA)}	START condition hold time	4.0		0.6		
t _{su(STA)}	Repeated START condition setup time	4.7		0.6		μs
t _{su(STO)}	STOP condition setup time	4.0		0.6		μs
t _{w(STO:STA)}	STOP to START condition time (bus free)	4.7		1.3		μs
C _b	Capacitive load for each bus line		400		400	pF

Table 34. I2C Characteristics

Notes:

- 1. Data based on standard I²C protocol requirement, not tested in production.
- 2. The device must internally provide a hold time of at least 300ns for the SDA signal in order to bridge the undefined region of the falling edge of SCL.
- 3. The maximum hold time of the START condition has only to be met if the interface does not stretch the low



period of SCL signal.

- 4. Measurement points are done at CMOS levels: $0.3xV_{DD}$ and $0.7xV_{DD}$.
- 5. f_{PCLK1} , must be at least 8MHz to achieve max fast I²C speed (400kHz).
- The following table gives the values to be written in the I2CCCR register to obtain the required I²C SCL line frequency.

Figure 33. Typical Application with I²C Bus and Timing Diagram⁴⁾



Table 35. SCL Frequency Table (f_{PCLK1} =8 MHz., V_{33} = 3.3 V)

f _{SCL}	I2CCCR Value
(kHz)	R _P =4.7kΩ
400	83
300	85h
200	8Ah
100	24h
50	4Ch
20	C4h

Legend:

 R_P = External pull-up resistance

 $f_{SCL} = I^2 C$ speed

NA = Not achievable

Note: For speeds around 200 kHz, achieved speed can have ±5% tolerance For other speed ranges, achieved speed can have ±2% tolerance The above variations depend on the accuracy of the external components used.



BSPI - Buffered Serial Peripheral Interface

Subject to general operating conditions for $V_{\text{DD}},\,T_{\text{A}}\,\text{and}\,f_{\text{PCLK}}$,unless otherwise specified.

Refer to *I/O port pin characteristics on page 50* for more details on the input/output alternate function characteristics (SS, SCK, MOSI, MISO).

Table 36.	BSPI characteristics	
-----------	-----------------------------	--

Symbol	Parameter	Conditions	Min	Мах	Unit
f _{scк}	CPI clock frequency	Master	f _{PCLK} /254	f _{PCLK} /6 5.5	MHz
1/t _{c(SCK)}	SPI clock frequency	Slave	0	f _{PCLK} /8 3.3	IVITIZ
t _{r(SCK)} t _{f(SCK)}	SPI clock rise and fall time	capacitive charge C=50 pF		14	
t _{su(SS)} ⁽¹⁾	SS setup time	Slave	0		
$t_{h(\overline{SS})}^{(1)}$	SS hold time	Slave	0		
t _{w(SCKH)} (1) t _{w(SCKL)} (1)	SCK high and low time	Master f _{PCLK} =33 MHz, presc = 6	73		
t _{su(MI)} (1) t _{su(SI)} (1)	Data input setup time	Master Slave	7 0		
t _{h(MI)} 1)(2) t _{h(SI)} 1)(2)	Data input hold time	Master Slave	1xt _{PCLK} 2xt _{PCLK}		
t _{h(MI)} (1) t _{h(SI)} (1)	Data input hold time	Master f _{PCLK} =33 MHz Slave f _{PCLK} =33 MHz	30 60		ns
t _{a(SO)} 1)(3)	Data output access time	Slave	0	1.5xt _{PCLK} +42	
la(SO)	Data output access time	Slave f _{PCLK} =33 MHz	0	87	
t _{dis(SO)} ⁽¹⁾⁽⁴⁾	Data output disable time	Slave	0	42	
t _{v(SO)} (1)(2)	Data output valid time	Slave (after enable edge)		3xt _{PCLK} +45	
v(SO)		f _{PCLK} =33 MHz		135	
t _{h(SO)} ⁽¹⁾	Data output hold time	Slave (after enable edge)	0		
t _{v(MO)} ⁽¹⁾⁽²⁾	Data output valid time	Master (after enable edge)		2xt _{PCLK} +12	
ν(MO) ` ´ ` ΄		f _{PCLK} =33 MHz		72	
t _{h(MO)} ⁽¹⁾	Data output hold time	Master (after enable edge)	0		

1. Data based on design simulation and/or characterisation results, not tested in production.

2. Depends on f_{PCLK} . For example, if f_{PCLK} =8MHz, then t_{PCLK} = 1/ f_{PLCLK} =125ns and $t_{v(MO)}$ = 255ns.

3. Min. time is the minimum time to drive the output and the max. time is the maximum time to validate the data.

4. Min time is the minimum time to invalidate the output and the max time is the maximum time to put the data in Hi-Z.











Figure 36. SPI Master Timing Diagram^(a)



a. Measurement points are done at CMOS levels: $0.3 x V_{33}$ and $0.7 x V_{33}$

USB Characteristics

The USB interface is USB-IF certified (Low Speed and Full Speed).

5.3.9 ADC characteristics

Subject to general operating conditions for AV_{DD} , f_{PCLK2} , and T_A unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ ¹⁾	Max	Unit
f _{MOD}	Modulator Oversampling frequency				2.1	MHz
V _{AIN}	Conversion voltage range ²⁾³⁾		0		2.5	V
l _{lkg}	Negative input leakage current on analog pins	V _{IN} <v<sub>SS, I I_{IN} I< 400µA on adjacent analog pin</v<sub>		5	6	μA
PBR	Passband Ripple				0.1	dB
SINAD	S/N and Distortion		56	63		dB
THD	Total Harmonic Distortion		60	74		dB
Z _{IN}	Input Impedance	f _{MOD} = 2 MHz	1			MΩ
C _{ADC}	Internal sample and hold capacitor				3.2	pF
t _{CONV}	Total Conversion time (including sampling time)		4096/ f _{MOD} (max)			
luna	Normal mode	T _A = 27 °C		2.5	3.0	mA
I _{ADC}	Standby mode	$T_A = 27 \ ^\circ C$			1	μA

Table 37.ADC characteristics

Notes:

- 1. Unless otherwise specified, typical data are based on $T_A=25^{\circ}C$ and $AV_{DD}-AV_{SS}=3.3V$. They are given only as design guidelines and are not tested.
- 2. Any added external serial resistor will downgrade the ADC accuracy (especially for resistance greater than 10kΩ). Data based on characterization results, not tested in production.
- 3. Calibration is needed once after each power-up.



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
ADC_DATA(0V)	Converted code when AIN=0V ¹⁾		2370		2565	Dec- imal
ADC_DATA(2.5V)	Converted code when AIN=2.5V ¹⁾		1480		1680	code
VCM	Center voltage of Sigma-Delta Modulator ¹⁾		1.23	1.25	1.30	V
TUE	Total unadjusted error	In this type of ADC, cal gain error and offset er limited to the ILE.			,	
IE _D I	Differential linearity error ¹⁾			1.96	2.19	LSB
IE _L I Integral linearity error ¹⁾				2.36	3.95	130

Table 38. ADC Accuracy with f_{PCLK2} = 20MHz, f_{ADC}=10MHz, AV_{DD}=3.3V

1. Data based on characterisation, not tested in production.

ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (nonrobust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. The effect of negative injection current on robust pins is specified in *Section 5.3.5*.

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 5.3.5* does not affect the ADC accuracy.





Analog power supply and reference pins

The AV_{DD} and AV_{SS} pins are the analog power supply of the A/D converter cell. They act as the high and low reference voltages for the conversion.

Separation of the digital and analog power pins allow board designers to improve A/D performance. Conversion accuracy can be impacted by voltage drops and noise in the event of heavily loaded or badly decoupled power supply lines (see: *General PCB design guidelines*).

General PCB design guidelines

To obtain best results, some general design and layout rules should be followed when designing the application PCB to shield the noise-sensitive, analog physical interface from noise-generating CMOS logic signals.

- Use separate digital and analog planes. The analog ground plane should be connected to the digital ground plane via a single point on the PCB.
- Filter power to the analog power planes. It is recommended to connect capacitors, with good high frequency characteristics, between the power and ground lines, placing 0.1µF and optionally, if needed 10pF capacitors as close as possible to the STR7 power supply pins and a 1 to 10µF capacitor close to the power source (see *Figure 38*).
- The analog and digital power supplies should be connected in a star network. Do not use a resistor, as AV_{DD} is used as a reference voltage by the A/D converter and any resistance would cause a voltage drop and a loss of accuracy.
- Properly place components and route the signal traces on the PCB to shield the analog inputs. Analog signals paths should run over the analog ground plane and be as short as possible. Isolate analog signals from digital signals that may switch while the analog inputs are being sampled by the A/D converter. Do not toggle digital outputs near the A/D input being converted.

Software filtering of spurious conversion results

For EMC performance reasons, it is recommended to filter A/D conversion outliers using software filtering techniques.



Figure 38. Power Supply Filtering

6 Package characteristics

6.1 Package mechanical data

Figure 39. 64-Pin Low Profile Quad Flat Package (10x10)





Figure 40. 144-Pin Low profile Quad Flat Package





Figure 41. 64-Low Profile Fine Pitch Ball Grid Array Package









Dpad	0.37 mm
Dsm	0.52 mm typ. (depends on solder mask registration tolerance
Solder paste	0.37 mm aperture diameter
 Non solder 	mask defined pads are recommended
– 4 to 6 mils s	creen print

6.2 Thermal characteristics

The average chip-junction temperature, T_J , in degrees Celsius, may be calculated using the following equation:

$$T_{J} = T_{A} + (P_{D} \times \Theta_{JA})$$
(1)

Where:

- T_A is the Ambient Temperature in °C,
- Θ_{JA} is the Package Junction-to-Ambient Thermal Resistance, in °C/W,
- P_D is the sum of P_{INT} and $P_{I/O} (P_D = P_{INT} + P_{I/O})$,
- P_{INT} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the Chip Internal Power.

P_{I/O} represents the Power Dissipation on Input and Output Pins;

Most of the time for the application $P_{I/O} < P_{INT}$ and can be neglected. On the other hand, $P_{I/O}$ may be significant if the device is configured to drive continuously external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_{\rm D} = K / (T_{\rm J} + 273^{\circ} {\rm C})$$
 (2)

Therefore (solving equations 1 and 2):

$$K = P_D x (T_A + 273^{\circ}C) + \Theta_{JA} x P_D^2$$
 (3)

where:

K is a constant for the particular part, which may be determined from equation (3) by measuring P_D (at equilibrium) for a known $T_{A_.}$ Using this value of K, the values of P_D and T_J may be obtained by solving equations (1) and (2) iteratively for any value of T_A .

Table 39. Thermal characteristics

Symbol	Parameter	Value	Unit
Θ _{JA}	Thermal Resistance Junction-Ambient LQFP 144 - 20 x 20 mm / 0.5 mm pitch	42	°C/W
Θ _{JA}	Thermal Resistance Junction-Ambient LQFP 64 - 10 x 10 mm / 0.5 mm pitch	45	°C/W
Θ _{JA}	Thermal Resistance Junction-Ambient LFBGA 64 - 8 x 8 x 1.7mm	58	°C/W
Θ _{JA}	Thermal Resistance Junction-Ambient LFBGA 144 - 10 x 10 x 1.7mm	50	°C/W

7 Product history

There are three versions of the STR710F series products. All versions are functionally identical and differ only with the points listed below.

Version "A" was the first version produced and delivered. Version "Z" was the second in production replacing version "A". Version "Z" has lower power consumption in STOP mode.

Version "X" is the latest introduced.

Marking

The difference between versions is visible on the marking of the product as shown in the four examples in *Figure 44* through *Figure 47*.







Table 40. A, Z and X version differences

Feature	A version	Z version	X version
ARM7TDMI core device Identification (ID) code register (see ARM7TDMI Technical Reference Manual)	Version bits [31:28] = 0001	Version bits [31:28] = 0010	Version bits [31:28] = 0010
Low power mode consumption in STOP mode at 25 °C	Not guaranteed Typical 49 µA	50 μA maximum at 25°C. Less than 30 μA at 25 °C for 99.730020% of parts	Same as Z.
SC.DATA pin	Not TRUE open drain When addressing 5V cards, the SCDATA Line must be connected to an open drain buffer.		Pin P0.10/U1.RX/U1.TX/SC. DATA has been modified to offer TRUE OPEN DRAIN functionality when in SmartCard mode. When addressing 5V cards, the SCDATA line can now be connected directly to the card I/O. This modification is backward compatible with previous designs, and no board modification is required.



8 Order codes

Partnumber	FLASH Kbytes	RAM Kbyte s	ЕМІ	USB	CAN	I/O Ports	Package	Temp. Range		
STR710FZ1T6	128+16	32								
STR710FZ2T6	256+16	64	Yes	Yes	Yes	48	LQFP144 20 x 20			
STR710RZT6	0	64								
STR710FZ1H6	128+16	32								
STR710FZ2H6	256+16	64	Yes	Yes	Yes Yes	Yes 48	LFBGA144 10 x 10 1.7			
STR710RZH6	0	64								
STR711FR0H6	64+16	16								
STR711FR1H6	128+16	32						LFBGA64 8 x 8 1.7		
STR711FR2H6	256+16	64		Yes	Yes No	30				
STR711FR0T6	64+16	16		fes no	30		-40 to +85°C			
STR711FR1T6	128+16	32						LQFP64 10x10		
STR711FR2T6	256+16	64								
STR712FR0H6	64+16	16					LFBGA64 8 x 8 1.7			
STR712FR1H6	128+16	32	No		Yes					
STR712FR2H6	256+16	64	No	INO						
STR712FR0T6	64+16	16			165					
STR712FR1T6	128+16	32		No		32	LQFP64 10 x10			
STR712FR2T6	256+16	64			32	32				
STR715FR0H6	64+16	16					LFBGA64 8 x 8 1.7			
STR715FR0T1	64+16	16			No		LQFP64 10 x 10	0 to 70°C		
STR715FR0T6	64+16	16								-40 to +85°C



9 Revision history

Table 42.	Document revision history
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Date	Revision	Changes
17-Mar-2004	1	First Release
05-Apr-2004	2	Updated "Electrical parameters" on page 33
08-Apr-2004	2.1	Corrected STR712F Pinout. Pins 43/42 swapped.
15-Apr-2004	2.2	PDF hyperlinks corrected.
7-Jul-2004	3	Corrected description of STDBY, V18, VSS18 V18BKP VSSBKP pins Added IDDrun typical data Updated BSPI max. baudrate. Updated "EMI - External Memory Interface" on page 56
29-Oct-2004	4	Corrected Flash sector B1F0/F1 address in <i>Figure 6: Memory</i> <i>map on page 30</i> Corrected <i>Table 6 on page 24</i> LQFP64 TEST pin is 16 instead of 17. Added to TQPFP64 column: pin 7 BOOTEN, pin 17 V _{33IO-PLL} Changed description of JTCK from 'External pull-down required' to 'External pull-up or pull down required'.
25-Jan-2005	5	Changed "Product Preview" to "Preliminary Data" on page 1 and 3 Renamed 'PU/PD' column to 'Reset state' in <i>Table 6 on</i> <i>page 24</i> Added reference to STR7 Flash Programming Reference Manual
19-Apr-2005 6		Added STR715F devices and modified RAM size of STR71xF1 devices Added BGA package in <i>Section 6</i> Updated ordering information in <i>Section 8</i> . Added PLL duty cycle min and max. in <i>PLL electrical</i> <i>characteristics on page 44</i>
13-Oct-2005 7		Updated feature description on page 1 Update overview <i>Section 1.1</i> Added OD/PP to P0.12 in <i>Table 6</i> Changed name of WFI mode to WAIT mode Changed Memory Map <i>Table 6</i> : Ext. Memory changed to 64 MB and flash register changed to 36 bytes. Added Power Consumption <i>Table 14</i> Modified BGA144 F3, F5, F12 and G12 in <i>Table 2</i> and <i>Table 3</i> Update EMI Timing <i>Table 25</i> and <i>Figure 29</i>



Table 42. Document revision history

Date	Revision	Changes
22-May-2006	8	Added Flashless device. Changed reset state of pins P1.10 and P1.13 from pu to pd, P0.15 from pu to floating and removed x in interrupt column for P1.15 and P1.12 in <i>Table 3</i> and <i>Table 6</i> Added notes under <i>Table 3</i> on EMI pin reset state. Corrected inch value for d3 in <i>Figure 39</i> Added footprint diagrams in <i>Figure 39</i> and <i>Figure 42</i> Updated <i>Section 5: Electrical parameters</i>
01-Aug-2006	9	Flash data retention changed to 20 years at 85° C. Changed note 8 on page 19 Changed note 1 on page 45
06-Nov-2006	10	Added STR715FR0T1 in <i>Table 41: Order codes</i> P0.12 corrected in <i>Table 6 on page 24</i>
20-Mar-2007	11	Added characteristics of <i>BSPI</i> - <i>Buffered Serial Peripheral</i> <i>Interface on page 63</i> Updated <i>Table 22: Low-power mode wake-up timing on</i> <i>page 45</i>



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